

MOSFETs Silicon P-Channel MOS

SSM3J56ACT

1. Applications

· High-Speed Switching

2. Features

- (1) 1.2 V drive
- (2) Low drain-source on-resistance

 $: R_{DS(ON)} = 390 \text{ m}\Omega \text{ (max) } (@V_{GS} = -4.5 \text{ V})$

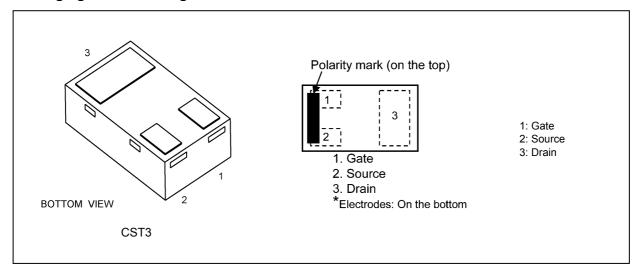
 $R_{\mathrm{DS(ON)}}$ = 480 m Ω (max) (@V_{GS} = -2.5 V)

 $R_{DS(ON)} = 660 \text{ m}\Omega \text{ (max) (@V_{GS} = -1.8 V)}$

 $R_{\rm DS(ON)}$ = 900 m Ω (max) (@ $V_{\rm GS}$ = -1.5 V)

 $R_{DS(ON)} = 4000 \text{ m}\Omega \text{ (max) (@V_{GS} = -1.2 V)}$

3. Packaging and Pin Assignment





4. Absolute Maximum Ratings (Note) (Unless otherwise specified, Ta = 25 °C)

Characteristics		Symbol	Rating	Unit
Drain-source voltage		V_{DSS}	-20	V
Gate-source voltage		V_{GSS}	±8	
Drain current (DC)	(Note 1)	I _D	-1.4	Α
Drain current (pulsed)	(Note 1), (Note 2)	I_{DP}	-2.8	
Power dissipation	(Note 3)	P_{D}	500	mW
Channel temperature		T _{ch}	150	°C
Storage temperature		T_{stg}	-55 to 150	

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

- Note 1: Ensure that the channel temperature does not exceed 150 °C.
- Note 2: Pulse width (PW) ≤ 10 ms, duty = 1 %
- Note 3: Device mounted on a 25.4 mm × 25.4 mm × 1.6 mm FR4 glass epoxy board (Cu pad: 645 mm²)

Note: This transistor is sensitive to electrostatic discharge and should be handled with care.

Note: The MOSFETs in this device are sensitive to electrostatic discharge. When handling this device, the worktables, operators, soldering irons and other objects should be protected against anti-static discharge.

Note: The channel-to-ambient thermal resistance, R_{th(ch-a)}, and the drain power dissipation, P_D, vary according to the board material, board area, board thickness and pad area. When using this device, be sure to take heat dissipation fully into account.

5. Electrical Characteristics

5.1. Static Characteristics (Unless otherwise specified, T_a = 25 °C)

Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current		I _{GSS}	$V_{GS} = \pm 8 \text{ V}, V_{DS} = 0 \text{ V}$	_	_	±1	μА
Drain cut-off current		I _{DSS}	V _{DS} = -20 V, V _{GS} = 0 V	_	_	-1	μА
Drain-source breakdown voltage		V _{(BR)DSS}	$I_D = -1 \text{ mA}, V_{GS} = 0 \text{ V}$	-20	_		V
Drain-source breakdown voltage	(Note 1)	V _{(BR)DSX}	I _D = -1 mA, V _{GS} = 5 V	-15	_	_	V
Gate threshold voltage	(Note 2)	V _{th}	$V_{DS} = -3 \text{ V}, I_{D} = -1 \text{ mA}$	-0.3	_	-1.0	V
Drain-source on-resistance	(Note 3)	R _{DS(ON)}	I_D = -800 mA, V_{GS} = -4.5 V	_	310	390	mΩ
			I _D = -500 mA, V _{GS} = -2.5 V	_	380	480	
			$I_D = -200 \text{ mA}, V_{GS} = -1.8 \text{ V}$	_	470	660	
			I _D = -100 mA, V _{GS} = -1.5 V	_	560	900	
			I _D = -10 mA, V _{GS} = -1.2 V	_	770	4000	
Forward transfer admittance	(Note 3)	Y _{fs}	$V_{DS} = -3 \text{ V}, I_{D} = -100 \text{ mA}$	0.5	1.0	_	S

Note 1: If a forward bias is applied between gate and source, this device enters V_{(BR)DSX} mode. Note that the drainsource breakdown voltage is lowered in this mode.

Note 2: Let V_{th} be the voltage applied between gate and source that causes the drain current (I_D) to below (-1 mA for this device). Then, for normal switching operation, V_{GS(ON)} must be higher than V_{th}, and V_{GS(OFF)} must be lower than V_{th}. This relationship can be expressed as: V_{GS(OFF)} < V_{th} < V_{GS(ON)}.

Take this into consideration when using the device.

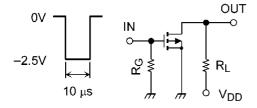
Note 3: Pulse measurement.



5.2. Dynamic Characteristics (Unless otherwise specified, T_a = 25 °C)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Input capacitance	C _{iss}	V _{DS} = -10 V, V _{GS} = 0 V,	_	100	_	pF
Reverse transfer capacitance	C _{rss}	f = 1 MHz	_	10	_	
Output capacitance	C _{oss}		_	16	_	
Switching time (turn-on time)	t _{on}	V_{DD} = -10 V, I_{D} = -200 mA V_{GS} = 0 to -2.5 V, R_{G} = 50 Ω	_	8	_	ns
Switching time (turn-off time)	t _{off}	Duty \leq 1 %, V_{IN} : t_r , t_f < 5 ns, Common source, See Chapter 5.3.	_	26	_	

5.3. Switching Time Test Circuit



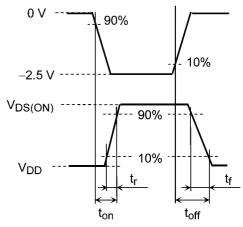


Fig. 5.3.1 Switching Time Test Circuit

Fig. 5.3.2 Input Waveform/Output Waveform

5.4. Gate Charge Characteristics (Unless otherwise specified, T_a = 25 °C)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Total gate charge (gate-source plus gate-drain)	Qg	V_{DD} = -10 V, V_{GS} = -4.5 V,		1.6	_	nC
Gate-source charge 1	Q _{gs1}	I _D = -800 mA	_	0.2	_	
Gate-drain charge	Q_{gd}			0.4		

5.5. Source-Drain Characteristics (Unless otherwise specified, T_a = 25 °C)

Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit
Diode forward voltage	(Note 1)	V_{DSF}	I _D = 1.4 A, V _{GS} = 0 V	_	1.0	1.3	V

Note 1: Pulse measurement.

6. Marking

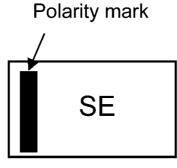


Fig. 6.1 Marking



7. Equivalent Circuit

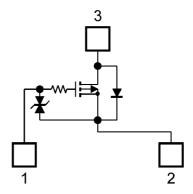


Fig. 7.1 Equivalent Circuit

8. Characteristics Curves (Note)

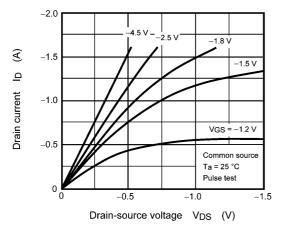


Fig. 8.1 I_D - V_{DS}

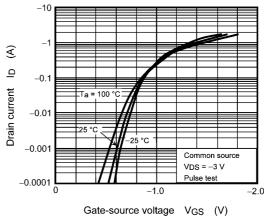


Fig. 8.2 I_D - V_{GS}

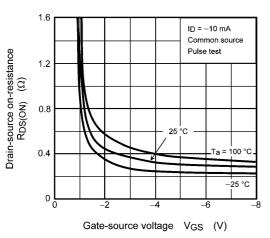


Fig. 8.3 R_{DS(ON)} - V_{GS}

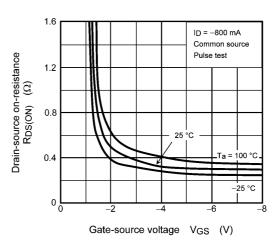


Fig. 8.4 R_{DS(ON)} - V_{GS}

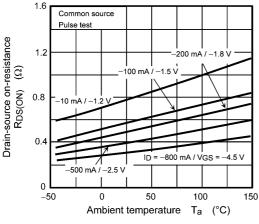


Fig. 8.5 R_{DS(ON)} - T_a

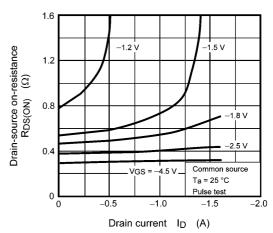


Fig. 8.6 R_{DS(ON)} - I_D

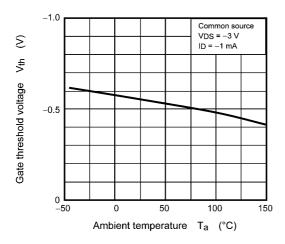


Fig. 8.7 V_{th} - T_a

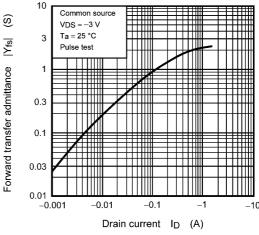


Fig. 8.8 |Yfs| - ID

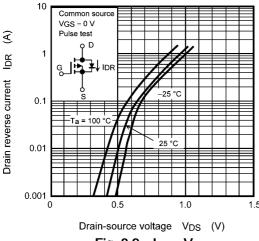


Fig. 8.9 IDR - VDS

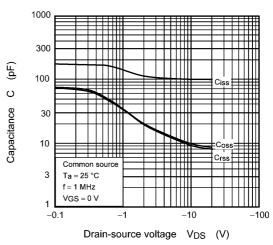
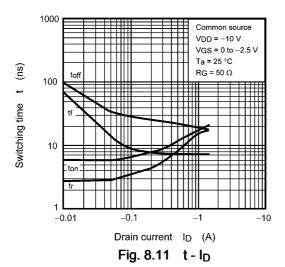
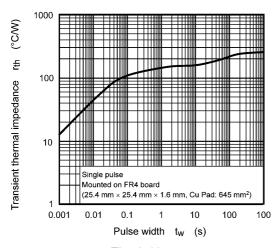


Fig. 8.10 C - V_{DS}



Common source

Fig. 8.12 Dynamic Input Characteristics



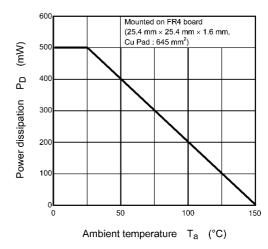


Fig. 8.13 rth - tw

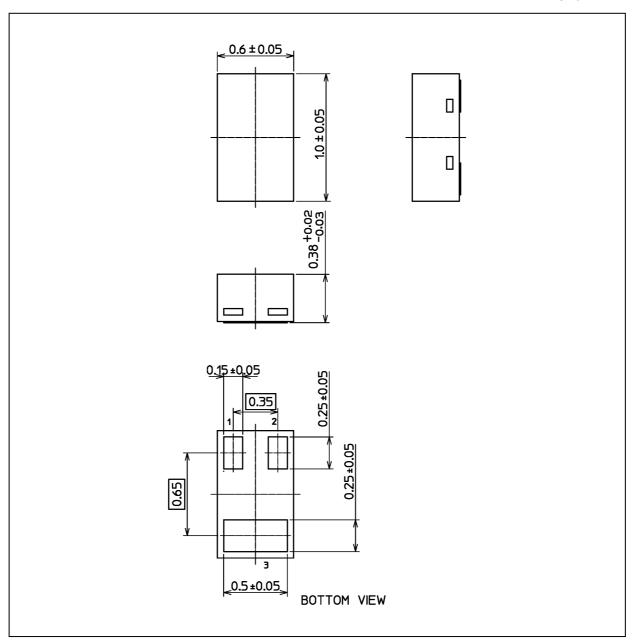
Fig. 8.14 PD - Ta

Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.



Package Dimensions

Unit: mm



Weight: 0.75 mg (typ.)

Package Name(s)
TOSHIBA: 1-1S1S
Nickname: CST3



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